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Kind regards,

Team Nexperia



PMV31XN

N-channel TrenchMOS FET

Rev. 2 — 30 November 2011

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology

1.3 Applications

- Battery-powered motor control
- High-speed switching in set top box power supplies

1.4 Quick reference data

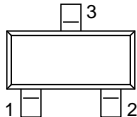
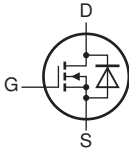
Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|----------------------------------|--|-----|-----|-----|------------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$ | - | - | 20 | V |
| I_D | drain current | $T_{sp} = 25\text{ °C}$; $V_{GS} = 4.5\text{ V}$; see Figure 2 ; see Figure 3 | - | - | 5.9 | A |
| P_{tot} | total power dissipation | $T_{sp} = 25\text{ °C}$; see Figure 1 | - | - | 2 | W |
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 2.5\text{ V}$; $I_D = 1\text{ A}$; $T_j = 25\text{ °C}$; see Figure 9 ; see Figure 10 | - | 44 | 53 | m Ω |
| | | $V_{GS} = 4.5\text{ V}$; $I_D = 1.5\text{ A}$; $T_j = 25\text{ °C}$; see Figure 9 ; see Figure 10 | - | 31 | 37 | m Ω |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|---|--|
| 1 | G | gate |  <p>SOT23 (TO-236AB)</p> |  <p>017aaa253</p> |
| 2 | S | source | | |
| 3 | D | drain | | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|----------|--|---------|
| | Name | Description | Version |
| PMV31XN | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| PMV31XN | %M4 |

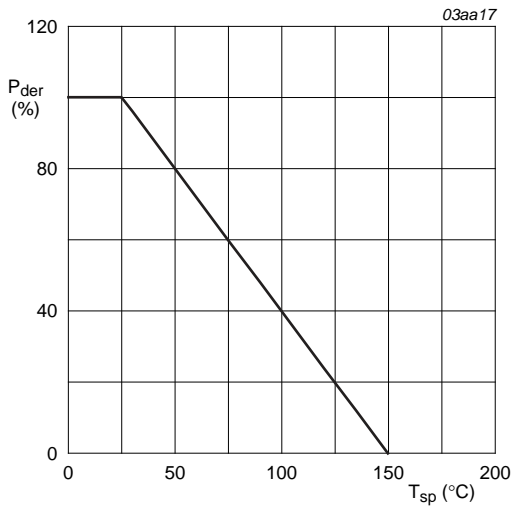
[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

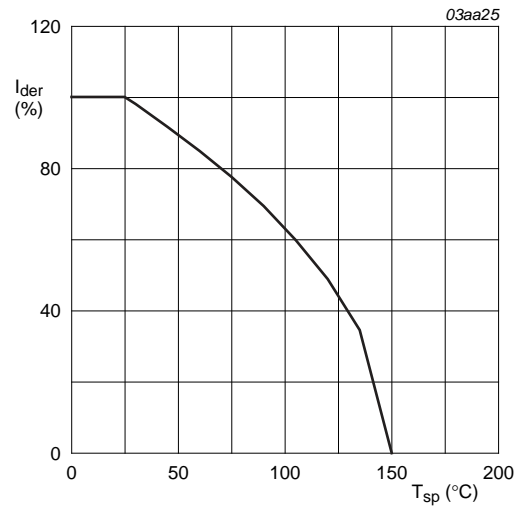
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------------|-------------------------|---|-----|------|------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$ | - | 20 | V |
| V_{DGR} | drain-gate voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$ | - | 20 | V |
| V_{GS} | gate-source voltage | | -12 | 12 | V |
| I_D | drain current | $T_{sp} = 100\text{ °C}$; $V_{GS} = 4.5\text{ V}$; see Figure 2 | - | 3.75 | A |
| | | $T_{sp} = 25\text{ °C}$; $V_{GS} = 4.5\text{ V}$; see Figure 2 ; see Figure 3 | - | 5.9 | A |
| I_{DM} | peak drain current | $T_{sp} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; see Figure 3 | - | 23.7 | A |
| P_{tot} | total power dissipation | $T_{sp} = 25\text{ °C}$; see Figure 1 | - | 2 | W |
| T_{stg} | storage temperature | | -55 | 150 | °C |
| T_j | junction temperature | | -55 | 150 | °C |
| Source-drain diode | | | | | |
| I_S | source current | $T_{sp} = 25\text{ °C}$ | - | 1.7 | A |



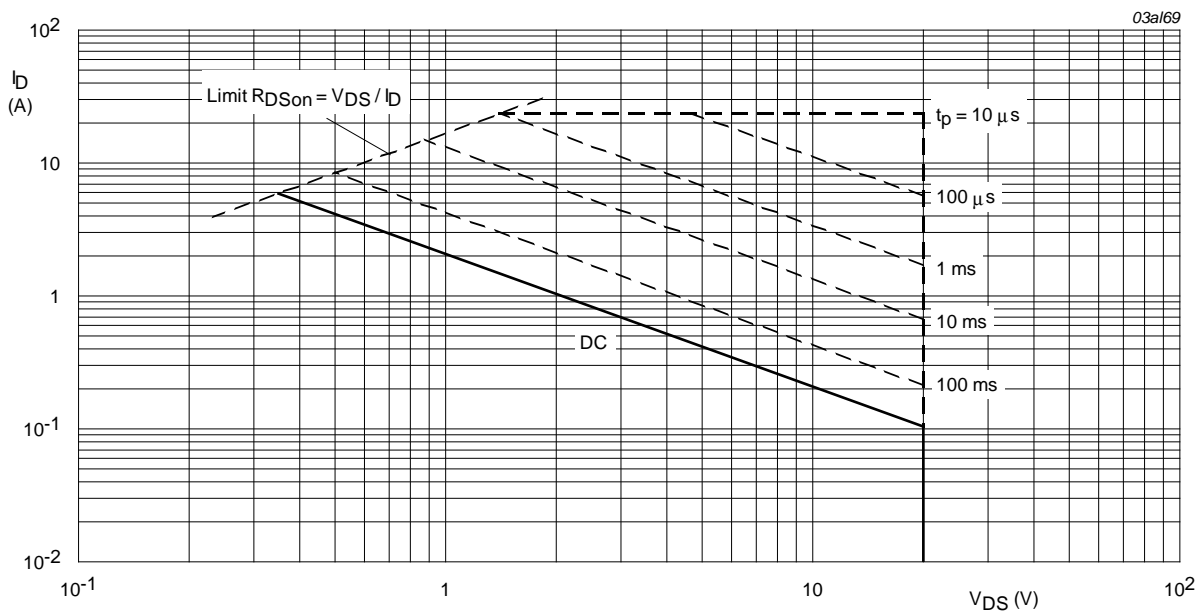
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature



$T_{sp} = 25^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|--|------------------------------|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | see Figure 4 | - | - | 60 | K/W |

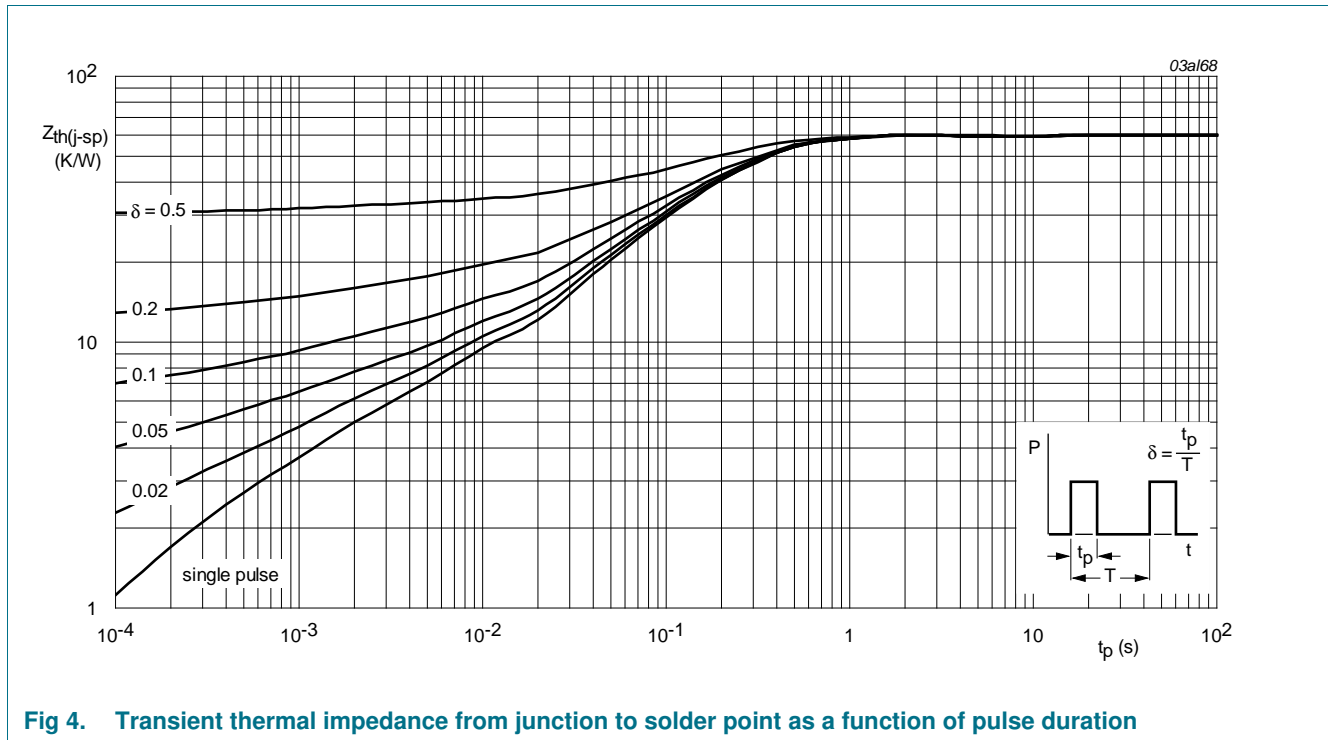


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

7. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---|------|------|-----|---------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$ | 18 | - | - | V |
| | | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | 20 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 8 | - | - | 1.8 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ\text{C};$ see Figure 8 | 0.35 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 8 | 0.5 | - | 1.5 | V |
| I_{DSS} | drain leakage current | $V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ }^\circ\text{C}$ | - | - | 100 | μA |
| | | $V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 1 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 10 | 100 | nA |
| | | $V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 10 | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 2.5 \text{ V}; I_D = 1 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 9 ; see Figure 10 | - | 44 | 53 | m Ω |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 1.5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 9 ; see Figure 10 | - | 31 | 37 | m Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 6 \text{ A}; V_{DS} = 10 \text{ V}; V_{GS} = 4.5 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 11 | - | 5.8 | - | nC |
| Q_{GS} | gate-source charge | | - | 1.4 | - | nC |
| Q_{GD} | gate-drain charge | | - | 1.7 | - | nC |
| C_{iss} | input capacitance | $V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 12 | - | 410 | - | pF |
| C_{oss} | output capacitance | | - | 115 | - | pF |
| C_{rss} | reverse transfer capacitance | | - | 80 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 10 \text{ V}; R_L = 10 \text{ } \Omega; V_{GS} = 4.5 \text{ V};$ $R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$ | - | 10 | - | ns |
| t_r | rise time | | - | 15 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 25 | - | ns |
| t_f | fall time | | - | 12 | - | ns |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 1.5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 13 | - | 0.75 | 1.2 | V |

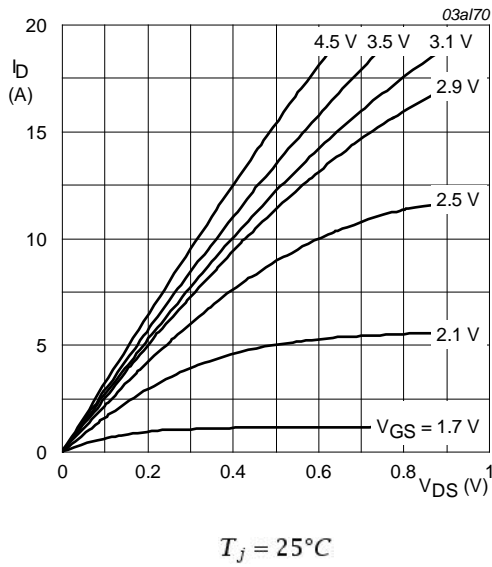


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

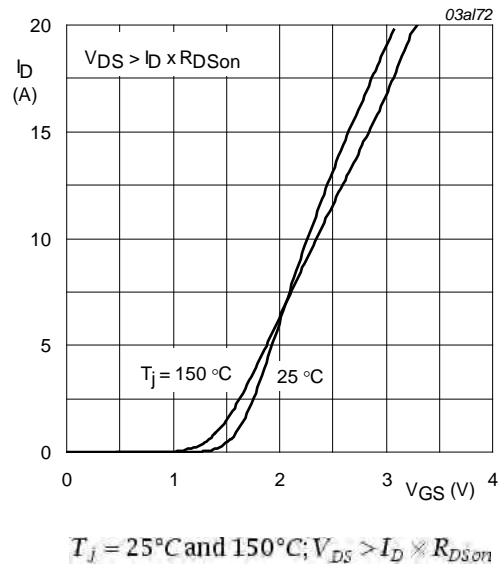


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

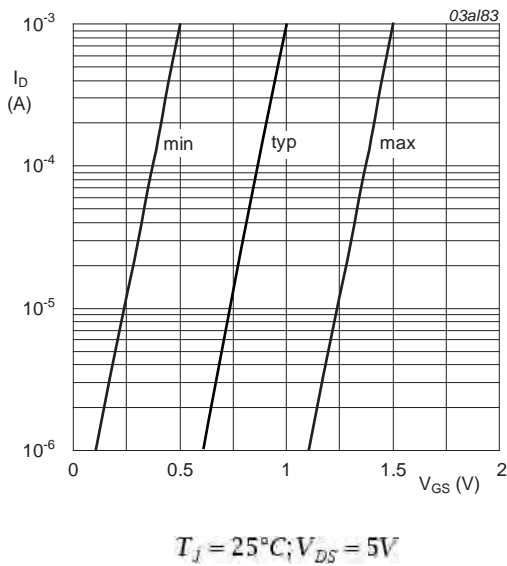


Fig 7. Sub-threshold drain current as a function of gate-source voltage

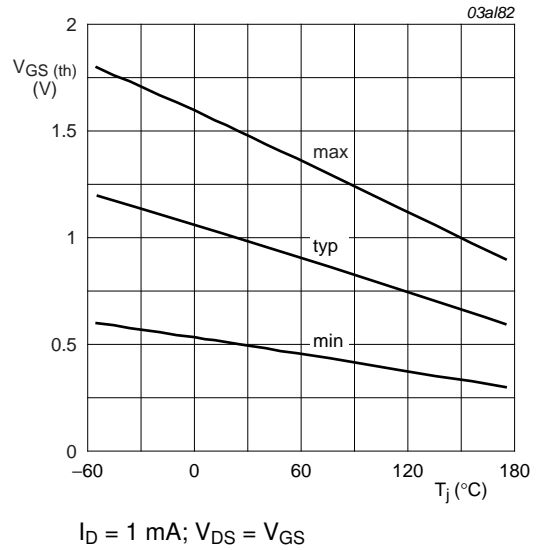
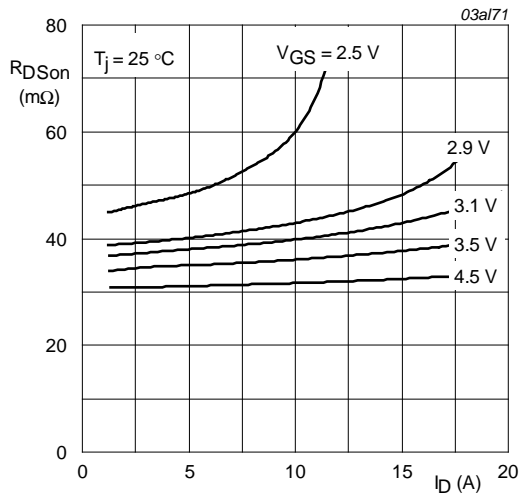
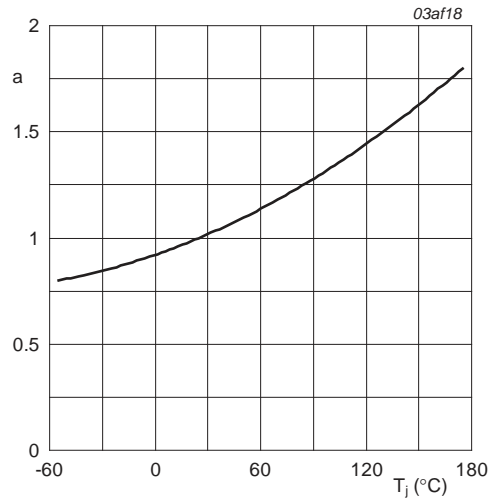


Fig 8. Gate-source threshold voltage as a function of junction temperature



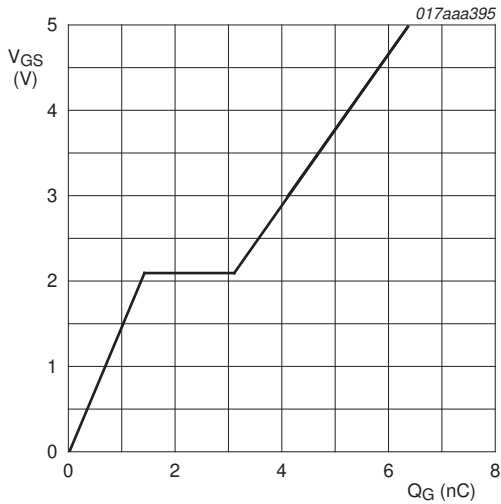
$T_j = 25\text{ }^\circ\text{C}$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



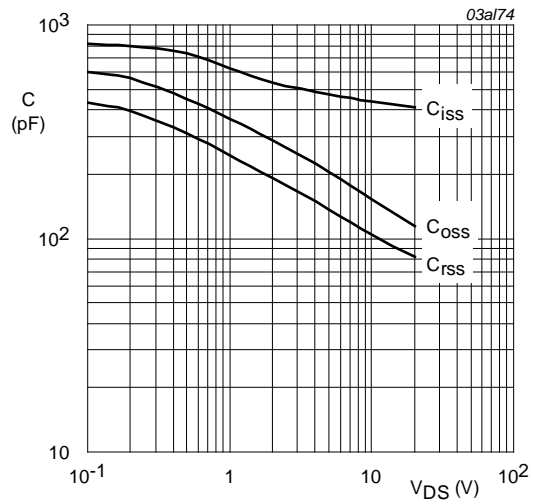
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



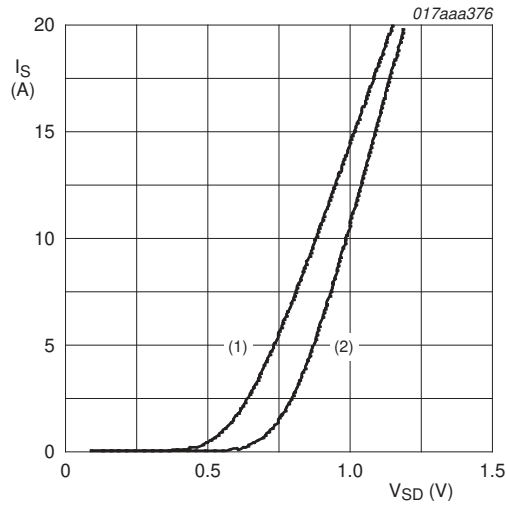
$I_D = 6\text{ A}; V_{DD} = 10\text{ V}; T_j = 25\text{ }^\circ\text{C}$

Fig 11. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{DS} > I_D \times R_{DS(on)}$

(1) T_j = 25 °C

(2) T_j = 150 °C

Fig 13. Source current as a function of source-drain voltage; typical values

8. Package outline

Plastic surface-mounted package; 3 leads

SOT23

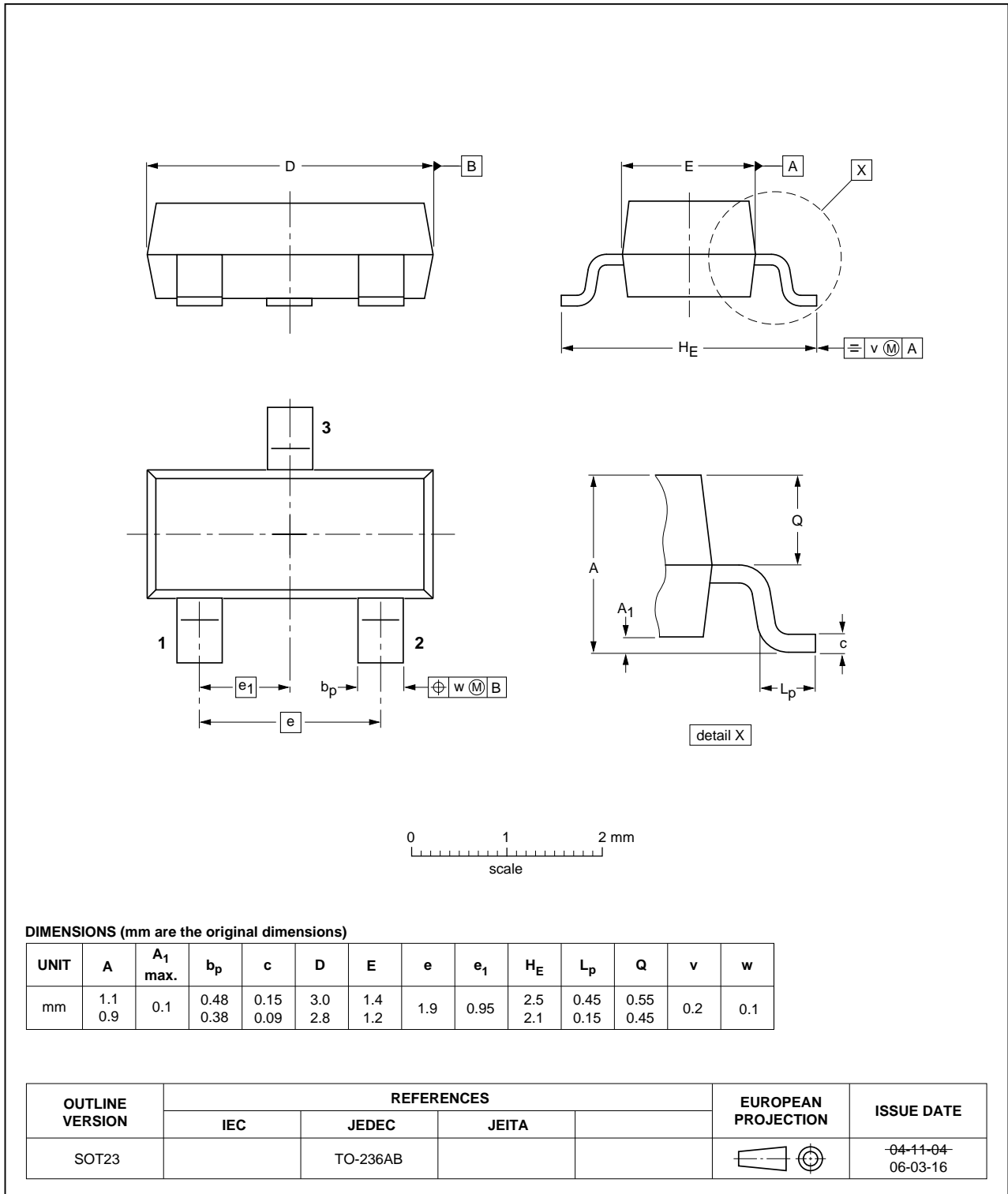


Fig 14. Package outline SOT23 (TO-236AB)

9. Soldering

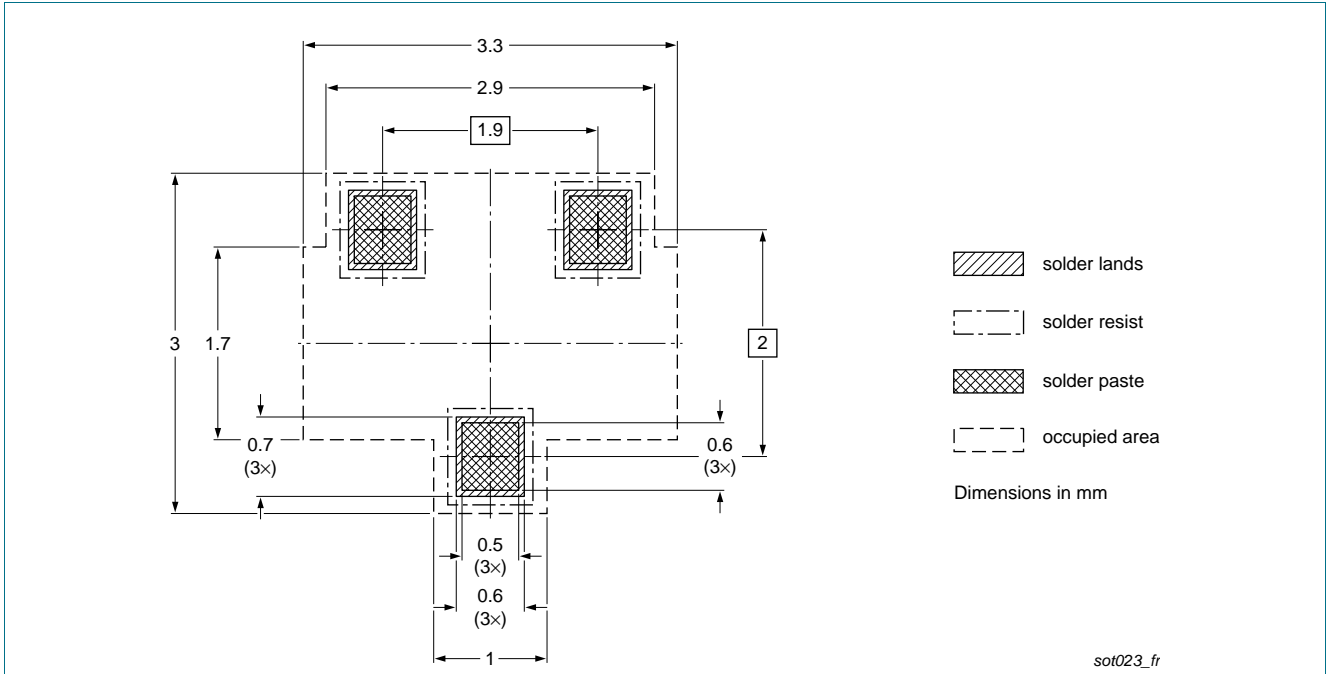


Fig 15. Reflow soldering footprint for SOT23 (TO-236AB)

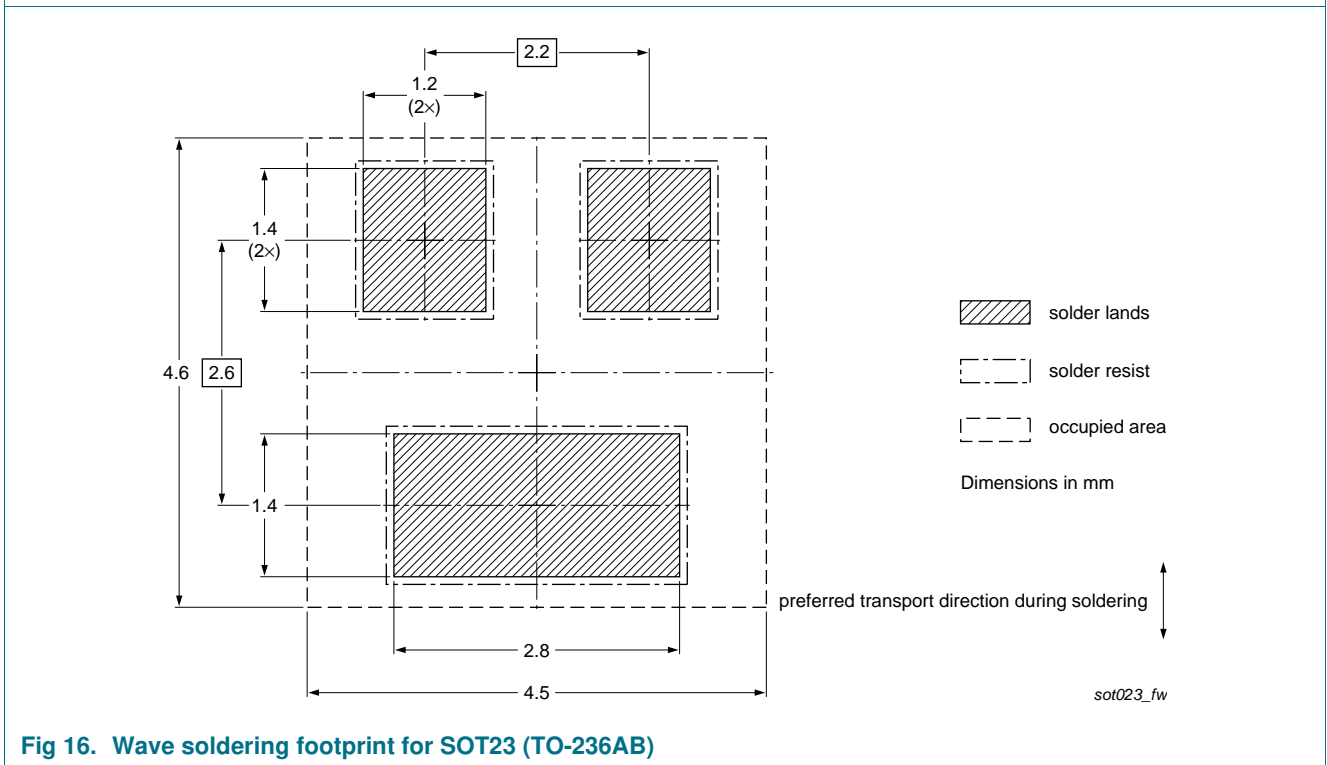


Fig 16. Wave soldering footprint for SOT23 (TO-236AB)

10. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|---|--------------------|---------------|-------------|
| PMV31XN v.2 | 20111130 | Product data sheet | - | PMV31XN v.1 |
| Modifications: | <ul style="list-style-type: none">• The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• 1 "Product profile": updated• 5 "Limiting values": V_{DSR} drain-source voltage redefined to V_{DGR} drain-gate voltage• 14 "Package outline SOT23 (TO-236AB)": updated• 9 "Soldering": added• 11 "Legal information": updated | | | |
| PMV31XN v.1 | 20030226 | Product data sheet | - | - |

11. Legal information

11.1 Data sheet status

| Document status ^[1] ^[2] | Product status ^[3] | Definition |
|---|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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